



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)} max	Ι <u></u> T _A = +25°C		
30V	30mΩ @ V _{GS} = 10V	6A		
307	40mΩ @ V _{GS} = 4.5V	4A		

Description and Applications

This new generation small-signal enhancement mode MOSFET features low on-resistance and fast switching, making it ideal for highefficiency power management applications.

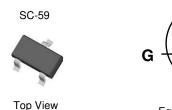
- Motor Control
- Backlighting
- **DC-DC Converters**
- **Power Management Functions**

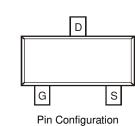
Features

- Low Gate Charge
- Low RDS(ON)
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP (Note 4)

Mechanical Data

- Case: SC-59
- Case Material Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
- Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.014 grams (Approximate)





Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3033LSNQ-7	SC-59	3,000/Tape & Reel
DMN3033LSNQ-13	SC-59	10,000/Tape & Reel

S

Equivalent Circuit

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

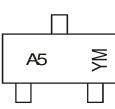
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



A5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Kev

Balo boab hoy												
Year	2007		201	5	2016	2017	2018	201	9 2	2020	2021	2022
Code	U		С		D	E	F	G		Н	I	J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	30	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current (Note 6) Continuous	T _A = +25°C T _A = +70°C	ID	6 5	А	
Pulsed Drain Current (Note 7)		I _{DM}	24	А	
Body-Diode Continuous Current (Note 6)		ls	2.25	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Unit	Value	Characteristic			
W	1.4	Total Power Dissipation (Note 6)			
°C /W	90	Thermal Resistance, Junction to Ambient (Note 6) t ≤10s			
50 °C	-55 to +150	Operating and Storage Temperature Range			
Operating and Storage Temperature Range TJ, TSTG -55 to +150 °C Notes: 6. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤10s.					

6. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s. 7. Repetitive Rating, pulse width limited by junction temperature.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS	• ,				•		
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	—	V	$I_{D} = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$ (Note 9) $T_J = 55^{\circ}C$	I _{DSS}	—	_	1 5	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Body Leakage Current	I _{GSS}	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 20V$	
Gate Threshold Voltage	V _{GS(th)}	1.0	_	2.1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)			25 36	30 40	mΩ	V _{GS} = 10V, I _D = 6A V _{GS} = 4.5V, I _D = 5A	
Forward Transconductance (Note 8)	g fs	_	5	_	S	$V_{DS} = 10V, I_D = 8A$	
Diode Forward Voltage (Note 8)	V _{SD}		0.7	1.1	V	I _S = 2.25A, V _{GS} = 0V	
DYNAMIC PARAMETERS (Note 9)							
Total Gate Charge	Qg	_	10.5		nC	$V_{GS} = 5V, V_{DS} = 15V, I_D = 6A$	
Gate-Source Charge	Qgs	_	3.8	_	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6A$	
Gate-Drain Charge	Q _{gd}		2.9	_	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6A$	
Turn-On Delay Time	t _{D(on)}	_	11	_	ns		
Turn-On Rise Time	tr		7	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time		_	63	_	ns	$R_D=1.8\Omega,\ R_G=6\Omega$	
Turn-Off Fall Time	t _f		30	_	ns	1	
Input Capacitance	Ciss	_	755	_	pF		
Output Capacitance	Coss	_	136		pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance		_	108		pF		

Notes:

8. Test pulse width t = 300ms.
9. Guaranteed by design. Not subject to production testing.



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= 25°C

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T_A = -55°C

T_A = 125°C

3

f = 1 MHz V_{GS} = 0V

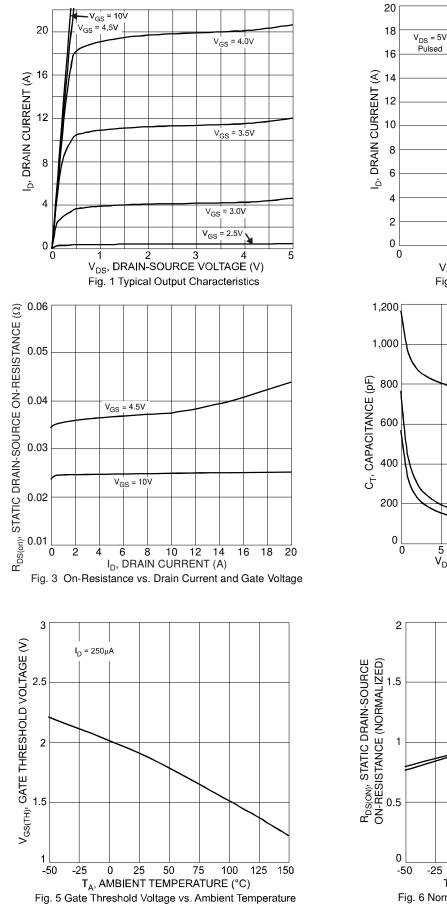
T_A = 85°C

2

V_{GS}, GATE-SOURCE VOLTAGE (V)

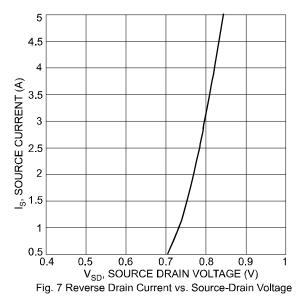
Fig. 2 Typical Transfer Characteristics

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C_{iss} C_{oss} $\rm C_{rss}$ 5 10 15 20 25 V_{DS}, DRAIN-SOURCE VOLTAGE (V) 30 Fig. 4 Typical Total Capacitance $V_{GS} = 10V$ I_D = 6A V_{GS} = 4.5V $I_D = 5A$ 25 50 75 100 125 150 -25 0 T_A, AMBIENT TEMPERATURE (C) Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



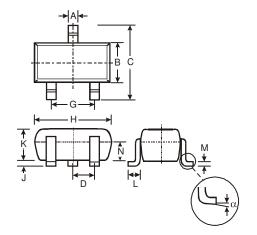


DMN3033LSNQ



Package Outline Dimensions

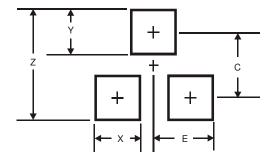
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SC-59						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	-	-	0.95			
G	-	-	1.90			
H	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
Ν	0.70	0.80	0.75			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Y	1.0
С	2.4
E	1.35



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